

**SPTECH Silicon NPN Power Transistor**

**2SD884**

**DESCRIPTION**

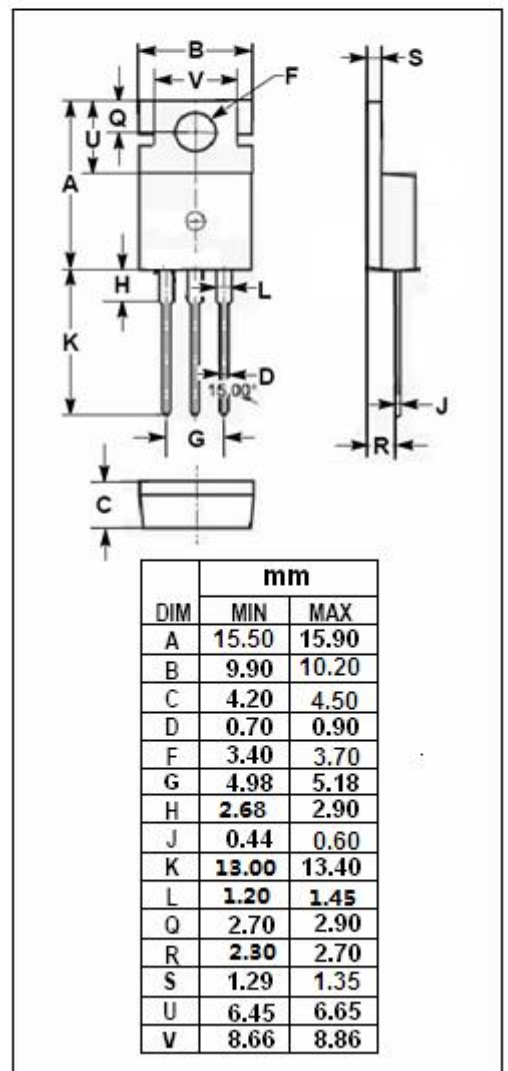
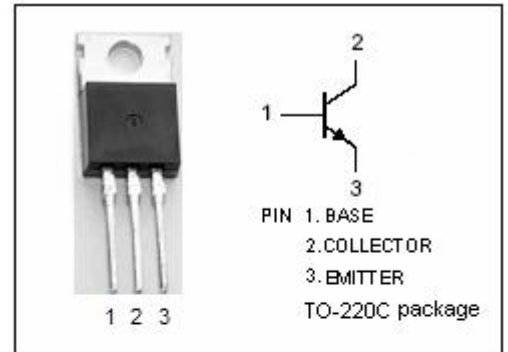
- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = 200V(\text{Min})$
- Low Collector-Emitter Saturation Voltage-  
:  $V_{CE(sat)} = 1.0V(\text{Max}) @ I_C = 0.5A$
- High speed switching

**APPLICATIONS**

- Designed for use in audio frequency power amplifier applications

**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	330	V
$V_{CEO}$	Collector-Emitter Voltage	200	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_C$	Collector Current-Continuous	7	A
$I_{CP}$	Collector Current-Peak	10	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	40	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



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**ELECTRICAL CHARACTERISTICS**

T<sub>c</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> =0.5A			1.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> =0.5A			1.2	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 330V ; I <sub>E</sub> = 0			100	μ A
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 6V ; I <sub>C</sub> = 0			1	mA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 5A ; V <sub>CE</sub> = 4V	10		45	
t <sub>f</sub>	Fall Time	I <sub>C</sub> = 5A , I <sub>B1</sub> = I <sub>B2</sub> = 800mA R <sub>B</sub> =0.5 Ω , -V <sub>EB</sub> =5V			0.75	μ s